

# **DATASHEET**

# ITR8307



#### **Features**

- Thin
- Fast response time
- High sensitivity
- Pb free
- High analytic
- Compact

# **Description**

The ITR8307 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black

thermoplastic housing The phototransistor receives radiation from the IR only .This is the normal situation. But when an object is in between, phototransistor could not receive the radiation.

#### **Applications**

- Various microcomputer control equipment
- Floppy disk driver
- Cassette type recorder
- Camera
- VCR



### **Device Selection Guide**

Device No.	Chip Material	LENS COLOR		
IR	GaAs	Water Clear		
PT	Silicon	Water Clear		

# Absolute Maximum Ratings (Ta=25)

Parameter		Symbol	Ratings	Unit
	Power Dissipation at(or below) 25 Free Air Temperature	Pd	75	mW
Inniii	Reverse Voltage	$V_R$	5	V
	Forward Current	$I_{\mathrm{F}}$	50	mA
	Peak Forward Current (*1) Pulse width 100 \mu s, Duty cycle=1%	$I_{\mathrm{FP}}$	1	A
Output	Collector Power Dissipation	$P_{C}$	75	mW
	Collector Current	$I_{C}$	50	mA
	Collector-Emitter Voltage	B V <sub>CEO</sub>	30	V
	Emitter-Collector Voltage	$\mathrm{B}\mathrm{V}_{\mathrm{ECO}}$	5	V
Operating Temperature		Topr	-25~+85	
Storage Temperature		Tstg	-30~+90	
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	

(\*1)  $tw=100 \mu sec.$ , T=10 msec. (\*2) t=5 Sec

**Expired Period: Forever** 



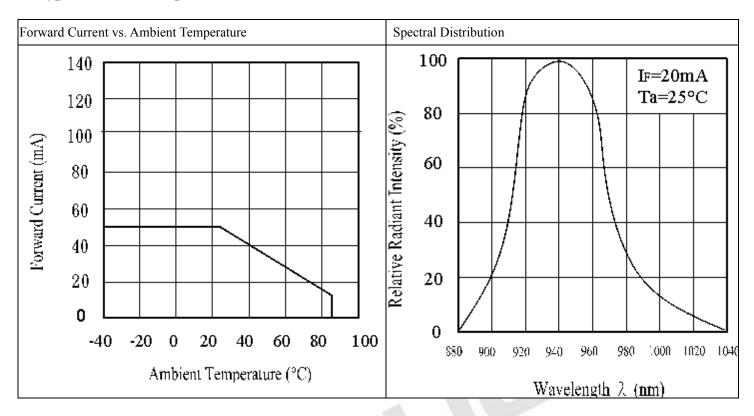
## **Electro-Optical Characteristics (Ta=25)**

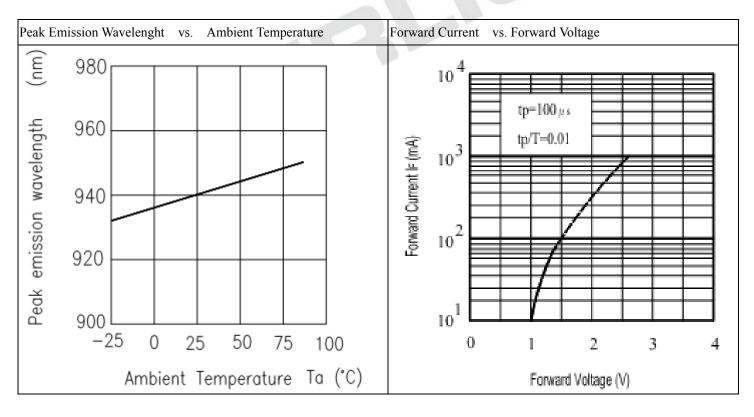
Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions			
	Forward Voltage	$V_{\mathrm{F}}$		1.2	1.6	V	I <sub>F</sub> =20mA			
Input	Reverse Current	$I_R$			10	μA	V <sub>R</sub> =5V			
	Peak Wavelength	P		940		nm	I <sub>F</sub> =20mA			
	View Angle	201/2		30		Deg	$I_F=20mA$			
	Dark Current	$I_{CEO}$			100	nA	$V_{CE}=10V$			
Output	C-E Saturation Voltage	V <sub>CE</sub> (sat)			0.4	V	$I_C=2mA$ Ee=1mW/cm <sup>2</sup>			
Transfer Characteristics	Collect Current	I <sub>C</sub> (ON)	0.1			mA	V <sub>CE</sub> =5V I <sub>F</sub> =20mA			
	Rise time	$t_{\rm r}$		20		µ sec	$V_{CE}=2V$ $I_{C}=100\mu A$			
	Fall time	$t_{\mathrm{f}}$		20		µ sec	$R_L=1K\Omega$			
Fall time $t_f$ 20 $\mu$ sec $R_L$ =1 $\kappa\Omega$										

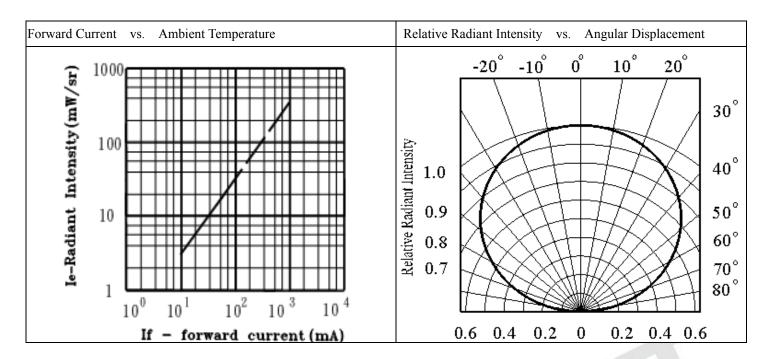
**Expired Period: Forever** 



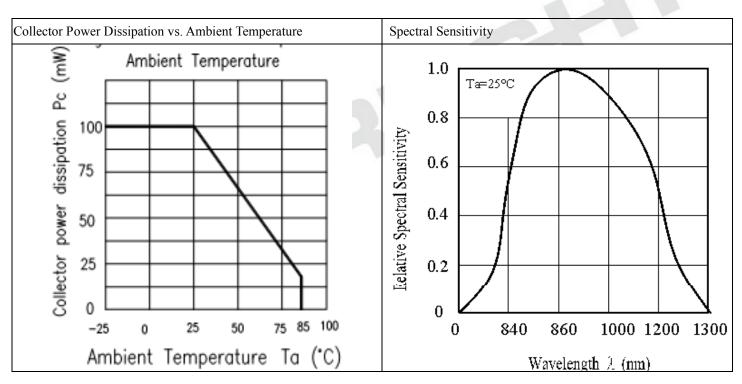
### Typical Electrical/Optical/Characteristics Curves for IR

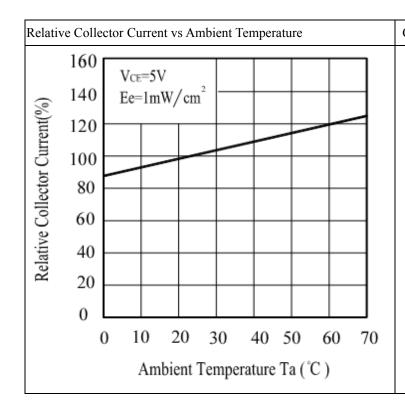


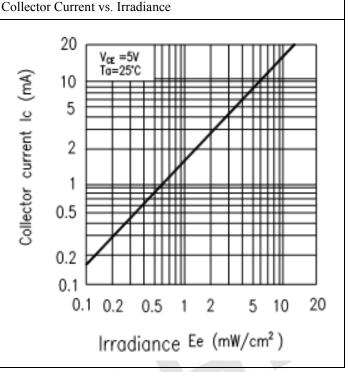


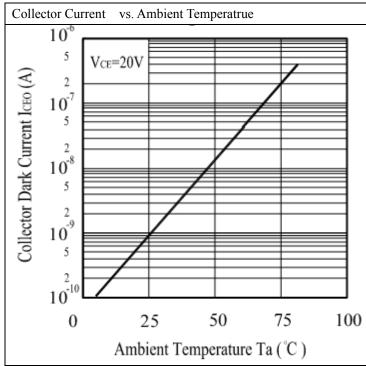


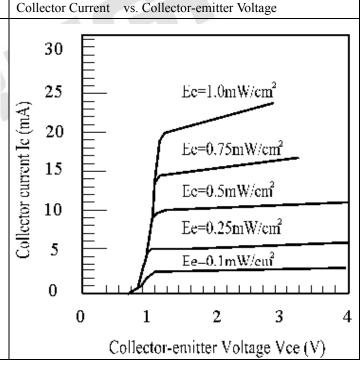
Typical Electro/Optical/Characteristics Curves for PT





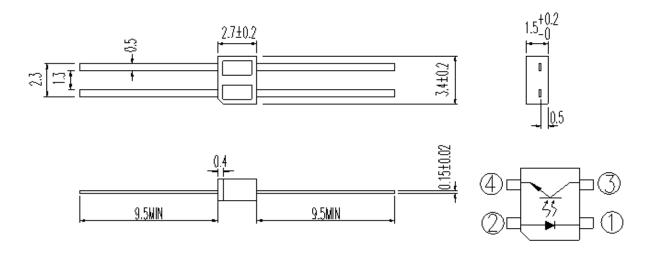








## **Package Dimension**



) :COLLECTOR

:CATHODE

:ANODE

Notes: 1.All dimensions are in millimeters

2. Tolerances unless dimensions ±0.25mm

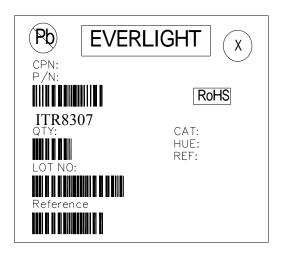
**Expired Period: Forever** 



#### **Packing Quantity Specification**

- 1. 1000pcs/1Bag
- 2. 1Bag/1Carton

#### **Label Form Specification**



- CPN: Customer's Product Number
- P/N: Product Number
- QTY: Packing Quantity
- · CAT: Luminous Intensity Rank
- HUE: Dom. Wavelength Rank
- REF: Forward Voltage Rank
- LOT No: Lot Number
- X: Month
- Reference: Identify Label Number

#### Notes

- 1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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